

Vishay Semiconductors

HEXFRED®, Ultrafast Soft Recovery Diode, 15 A



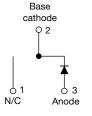


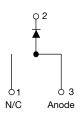
TO-263AB (D²PAK)

TO-262AA

VS-HFA15 TB60SPbF

VS-HFA15 TB60-1PbF

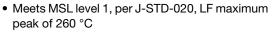




| PRODUCT SUMMARY | |
|----------------------------------|---|
| Package | TO-263AB (D ² PAK), TO-262AA |
| I _{F(AV)} | 15 A |
| V_{R} | 600 V |
| V _F at I _F | 1.2 V |
| t _{rr} (typ.) | 23 ns |
| T _J max. | 150 °C |
| Diode variation | Single die |

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}





Designed and qualified for industrial level

RoHS COMPLIANT

• AEC-Q101 qualified

HALOGEN S Of FREE

 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15TB60SPbF, VS-HFA15TB60-1PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

| ABSOLUTE MAXIMUM RATINGS | | | | | | | | | |
|--|-----------------------------------|-------------------------|-------------|-------|--|--|--|--|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | | | | | |
| Cathode to anode voltage | V_R | | 600 | V | | | | | |
| Maximum continuous forward current | I _F | T _C = 100 °C | 15 | | | | | | |
| Single pulse forward current | I _{FSM} | | 150 | Α | | | | | |
| Maximum repetitive forward current | I _{FRM} | | 60 | | | | | | |
| Maximum power discination | P _D | T _C = 25 °C | 74 | W | | | | | |
| Maximum power dissipation | | T _C = 100 °C | 29 |] vv | | | | | |
| Operating junction and storage temperature range | T _J , T _{Stg} | | -55 to +150 | °C | | | | | |



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| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|--|-----------------|--|-------------|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| Cathode to anode breakdown voltage | V _{BR} | I _R = 100 μA | | 600 | - | - | |
| Maximum forward voltage | | I _F = 15 A | | - | 1.3 | 1.7 | V |
| | V_{FM} | I _F = 30 A | See fig. 1 | - | 1.5 | 2.0 | |
| | | I _F = 15 A, T _J = 125 °C | | - | 1.2 | 1.6 | |
| Maximum reverse | 1 | V _R = V _R rated | See fig. 2 | - | 1.0 | 10 | |
| leakage current | I _{RM} | $T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$ | See lig. 2 | - | 400 | 1000 | μA |
| Junction capacitance | C _T | V _R = 200 V | See fig. 3 | - | 25 | 50 | pF |
| Series inductance | L _S | Measured lead to lead 5 mm from p | ackage body | - | 8.0 | - | nH |

| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | | |
|---|---------------------------|--|--|------|------|------|--------|--|
| PARAMETER | SYMBOL | TEST CON | IDITIONS | MIN. | TYP. | MAX. | UNITS | |
| | t _{rr} | $I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$ | Vμs, V _R = 30 V | - | 23 | - | ns | |
| Reverse recovery time See fig. 5 | t _{rr1} | T _J = 25 °C | | - | 50 | 60 | | |
| | t _{rr2} | T _J = 125 °C | $I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$ | - | 105 | 120 | | |
| Peak recovery current | I _{RRM1} | T _J = 25 °C | | - | 4.5 | 6.0 | A nC | |
| See fig. 6 | I _{RRM2} | T _J = 125 °C | | - | 6.5 | 10 | | |
| Reverse recovery charge | Q _{rr1} | T _J = 25 °C | | - | 84 | 180 | | |
| See fig. 7 | Q _{rr2} | T _J = 125 °C | | - | 241 | 600 | IIC | |
| Peak rate of fall of recovery current during the | dI _{(rec)M} /dt1 | T _J = 25 °C | | - | 188 | - | - A/μs | |
| See fig. 8 | dI _{(rec)M} /dt2 | T _J = 125 °C | | - | 160 | - | | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | | | |
|---|-------------------|--|-------------|------|------|-------|--|--|
| PARAMETER | SYMBOL | L TEST CONDITIONS | | TYP. | MAX. | UNITS | | |
| Lead temperature | T _{lead} | 0.063" from case (1.6 mm) for 10 s | - | - | 300 | °C | | |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 1.7 | | | |
| Thermal resistance, junction to ambient | R _{thJA} | Typical socket mount | - | - | 80 | K/W | | |
| Thermal resistance, case to heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.5 | - | | | |
| Weight | | | - | 2.0 | - | g | | |
| vveignit | | | - | 0.07 | - | oz. | | |
| Madina davia | | Case style D ² PAK | HFA15TB60S | | | | | |
| Marking device | | Case style TO-262 | HFA15TB60-1 | | | | | |





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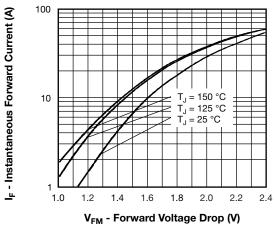


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

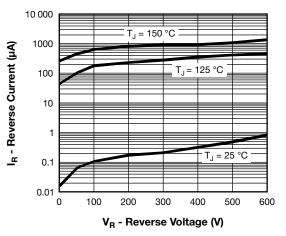


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

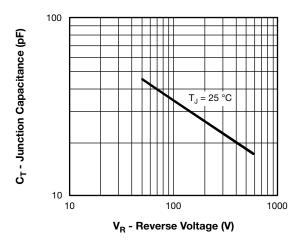


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

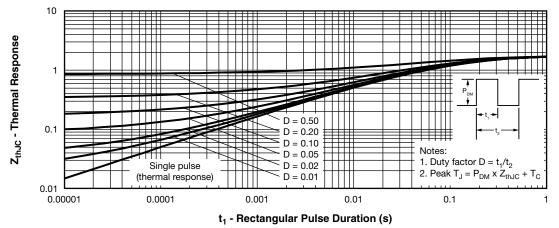


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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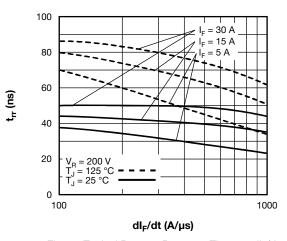


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

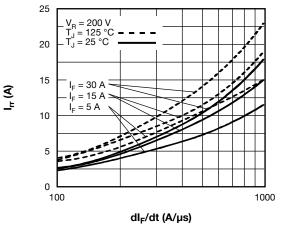


Fig. 6 - Typical Recovery Current vs. dl_F/dt

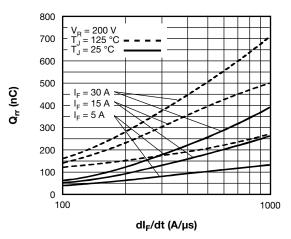


Fig. 7 - Typical Stored Charge vs. dl_F/dt

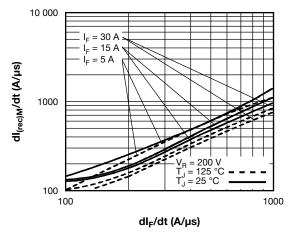


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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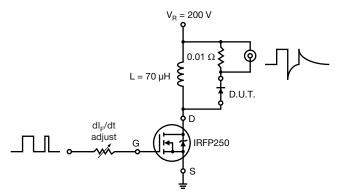
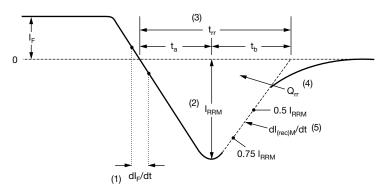


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

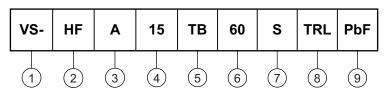
(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

Current rating (15 = 15 A)

5 - Package:

TB = TO-220

Voltage rating (60 = 600 V)

- • $S = D^2PAK$

- • -1 = TO-262

8 - • None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D2PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - PbF = lead (Pb)-free

- P = lead (Pb)-free (for D²PAK TRL and TRR)

| LINKS TO RELATED DOCUMENTS | | | | | | |
|----------------------------|---|--|--|--|--|--|
| Dimensions | TO-263AB (D ² PAK): www.vishay.com/doc?95046 | | | | | |
| Differences | TO-262AA: www.vishay.com/doc?95419 | | | | | |
| Part marking information | TO-263AB (D ² PAK): www.vishay.com/doc?95054 | | | | | |
| Fait marking information | TO-262AA: www.vishay.com/doc?95420 | | | | | |
| Packaging information | www.vishay.com/doc?95032 | | | | | |
| SPICE model | www.vishay.com/doc?95357 | | | | | |



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D²PAK

DIMENSIONS in millimeters and inches



| SYMBOL | MILLIMETERS | | INCHES NOTES SYMBOL | CVMDOL | MILLIM | ETERS | INC | HES | NOTES | | | |
|----------|-------------|-------|---------------------|--------|--------|------------|---------|-------|-------|-------|-------|-------|
| STIVIBUL | MIN. | MAX. | MIN. | MAX. | NOIES | NOTES STIM | STWIDOL | MIN. | MAX. | MIN. | MAX. | NOTES |
| Α | 4.06 | 4.83 | 0.160 | 0.190 | | | D1 | 6.86 | 8.00 | 0.270 | 0.315 | 3 |
| A1 | 0.00 | 0.254 | 0.000 | 0.010 | | | Е | 9.65 | 10.67 | 0.380 | 0.420 | 2, 3 |
| b | 0.51 | 0.99 | 0.020 | 0.039 | | | E1 | 7.90 | 8.80 | 0.311 | 0.346 | 3 |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 | 4 | | е | 2.54 | BSC | 0.100 |) BSC | |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 | | | Н | 14.61 | 15.88 | 0.575 | 0.625 | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | L | 1.78 | 2.79 | 0.070 | 0.110 | |
| С | 0.38 | 0.74 | 0.015 | 0.029 | | | L1 | - | 1.65 | - | 0.066 | 3 |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 | 4 | | L2 | 1.27 | 1.78 | 0.050 | 0.070 | |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 | | | L3 | 0.25 | BSC | 0.010 | BSC | |
| D | 8.51 | 9.65 | 0.335 | 0.380 | 2 | | L4 | 4.78 | 5.28 | 0.188 | 0.208 | |

Notes

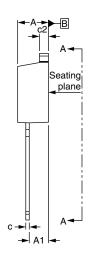
- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB

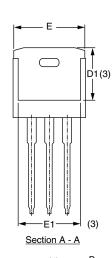


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TO-262

DIMENSIONS in millimeters and inches



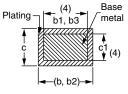


⊕ 0.010**⋒**|A**⋒**|B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode
3. - Anode



Section B - B and C - C Scale: None

| CVMPOL | MILLIN | METERS | INC | INCHES | | | |
|--------|----------|--------|-----------|--------|-------|--|--|
| SYMBOL | MIN. | MAX. | MIN. | MAX. | NOTES | | |
| А | 4.06 | 4.83 | 0.160 | 0.190 | | | |
| A1 | 2.03 | 3.02 | 0.080 | 0.119 | | | |
| b | 0.51 | 0.99 | 0.020 | 0.039 | | | |
| b1 | 0.51 | 0.89 | 0.020 | 0.035 | 4 | | |
| b2 | 1.14 | 1.78 | 0.045 | 0.070 | | | |
| b3 | 1.14 | 1.73 | 0.045 | 0.068 | 4 | | |
| С | 0.38 | 0.74 | 0.015 | 0.029 | | | |
| c1 | 0.38 | 0.58 | 0.015 | 0.023 | 4 | | |
| c2 | 1.14 | 1.65 | 0.045 | 0.065 | | | |
| D | 8.51 | 9.65 | 0.335 | 0.380 | 2 | | |
| D1 | 6.86 | 8.00 | 0.270 | 0.315 | 3 | | |
| Е | 9.65 | 10.67 | 0.380 | 0.420 | 2, 3 | | |
| E1 | 7.90 | 8.80 | 0.311 | 0.346 | 3 | | |
| е | 2.54 BSC | | 0.100 BSC | | | | |
| L | 13.46 | 14.10 | 0.530 | 0.555 | | | |
| L1 | = | 1.65 | - | 0.065 | 3 | | |
| L2 | 3.56 | 3.71 | 0.140 | 0.146 | | | |

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

Revision: 02-Oct-12 Document Number: 91000